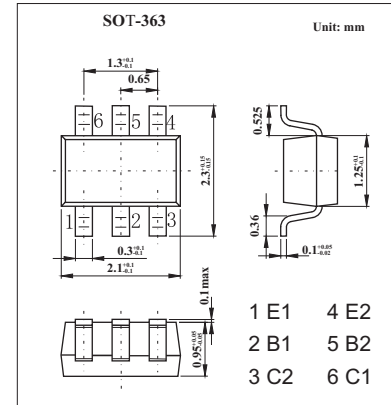
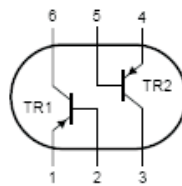


## PNP General Purpose Double Transistor

## KC856S(BC856S)

## ■ Features

- Two transistors in one package
- Reduces number of components and board space
- No mutual interference between the transistors.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	-80	V
Collector-Emitter Voltage	$V_{CE0}$	-65	V
Emitter-Base Voltage	$V_{EB0}$	-5	V
Collector Current - Continuous	$I_c$	-100	mA
Power Dissipation	$P_D$	200	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	416	$^\circ\text{C}/\text{W}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-Cutoff Current	$I_{CBO}$	$V_{CB} = -30\text{ V}, I_E = 0$			-15	nA
		$V_{CB} = -30\text{ V}, I_E = 0, T_A = 150^\circ\text{C}$			-5.0	$\mu\text{A}$
Emitter- cutoff current	$I_{EBO}$	$I_c = 0, V_{EB} = -5\text{ V}$			-100	nA
DC Current Gain	$h_{FE}$	$I_c = -2.0\text{ mA}, V_{CE} = -5.0\text{ V}$	110			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c = -10\text{ mA}, I_B = -0.5\text{ mA}$			-100	mV
		$I_c = -100\text{ mA}, I_B = -5.0\text{ mA}$			-300	mV
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_c = -10\text{ mA}, I_B = -0.5\text{ mA}$		700		mV
Output Capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}, f = 1.0\text{ MHz}$			2.5	pF
Transistion frequency	$f_T$	$I_c = -10\text{ mA}, V_{CE} = -5.0\text{ V}, f = 100\text{ MHz}$	100			MHz

## ■ Marking

Marking	5F